

产品变更说明

日期: 2022/8/24

编号: PNCMOS22082401

致尊敬的客户:

非常感谢你们使用 APM-MOSFET 产品, 由于我司部分产品为型号标识, 导致市场出现有假冒伪劣我司产品的产品。

AP9N20D/Y
N-Channel Enhancement MOSFET

Description
The AP9N20D is silicon N-channel Enhanced VMOSFETs, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency.

General Features
V_{DS} = 200V I_B = 9A
R_{DS(on)} < 300mΩ @ V_{GS}=10V

Application
Uninterruptible Power Supply(UPS)
Power Factor Correction (PFC)

Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{DS}	Drain-Source Voltage (V _{GS} =0V)	200	V
I _D	Continuous Drain Current ¹	9	A
IDM	Pulsed Drain Current (note1)	36	A
V _{GS}	Gate-Source Voltage	±20	V
E _{AS}	Single Pulse Avalanche Energy (note2)	100	mJ
I _{AR}	Avalanche Current (note1)	7.5	A
E _{sw}	Repetitive Avalanche Energy (note1)	8.1	mJ
P _D	Power Dissipation (T _c =25°C)	74	W
T _J Tstg	Operating Junction and Storage Temperature Range	-55~150	°C
R _{thJC}	Thermal Resistance, Junction-to-Case	1.7	°C/W
R _{thJA}	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

AP9N20D
200V N-Channel Enhancement Mode MOSFET

Description
The AP9N20D is silicon N-channel Enhanced VMOSFETs, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency.

General Features
V_{DS} = 200V I_B = 9A
R_{DS(on)} < 300mΩ @ V_{GS}=10V (Type: 230mΩ)

Application
Uninterruptible Power Supply(UPS)
Power Factor Correction (PFC)

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCs)
AP9N20D	TO-252-3L	AP9N20D XXX YYYY	2500

Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{DS}	Drain-Source Voltage (V _{GS} =0V)	200	V
I _D	Continuous Drain Current	9	A
IDM	Pulsed Drain Current (note1)	36	A
V _{GS}	Gate-Source Voltage	±20	V
E _{sw}	Single Pulse Avalanche Energy (note2)	100	mJ
I _{AR}	Avalanche Current (note1)	7.5	A
E _{sw}	Repetitive Avalanche Energy (note1)	8.1	mJ
P _D	Power Dissipation (T _c =25°C)	74	W
T _J Tstg	Operating Junction and Storage Temperature Range	-55~150	°C
R _{thJC}	Thermal Resistance, Junction-to-Case	1.7	°C/W
R _{thJA}	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

AP9N20D RVE1.0 永源微电子科技有限公司

AP6G04S
40V N+P-Channel Enhancement Mode MOSFET

Description
The AP6G04S uses advanced trench technology to provide excellent R_{DS(on)}, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features
V_{DS} = 40V I_B = 3A
R_{DS(on)} < 37mΩ @ V_{GS}=10V (Type: 30mΩ)
V_{GS} = 40V I_B = 6.1A
R_{DS(on)} < 75mΩ @ V_{GS}=10V (Type: 62mΩ)

Application
Wireless charging
Boost driver
Brushless motor

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCs)
AP6G04S	SO8	AP6G04S XXX YYYY	3000

Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
V _{DS}	Drain-Source Voltage	40	-40	V
V _{GS}	Gate-Source Voltage	±20	±20	V
I _D T _c =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	5.3	-6.1	A
I _D T _c =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	4.9	-4.5	A
I _{sw}	Pulsed Drain Current ²	23	-22	A
E _{AS}	Single Pulse Avalanche Energy ³	16.2	39	mJ
I _{AS}	Avalanche Current	6.8	-6.8	A
P _D T _c =25°C	Total Power Dissipation ⁴	1.67	1.67	W
T _{stg}	Storage Temperature Range	-55 to 150	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	-55 to 150	°C
R _{thJC}	Thermal Resistance Junction-Ambient ¹	7.5		°C/W
R _{thJC}	Thermal Resistance Junction-Case ¹	30		°C/W

AP6G04S
40V N+P-Channel Enhancement Mode MOSFET

Description
The AP6G04S uses advanced trench technology to provide excellent R_{DS(on)}, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features
V_{DS} = 40V I_B = 3A
R_{DS(on)} < 37mΩ @ V_{GS}=10V (Type: 30mΩ)
V_{GS} = 40V I_B = 6.1A
R_{DS(on)} < 75mΩ @ V_{GS}=10V (Type: 62mΩ)

Application
Wireless charging
Boost driver
Brushless motor

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCs)
AP6G04S	SO8	AP6G04S XXX YYYY	3000

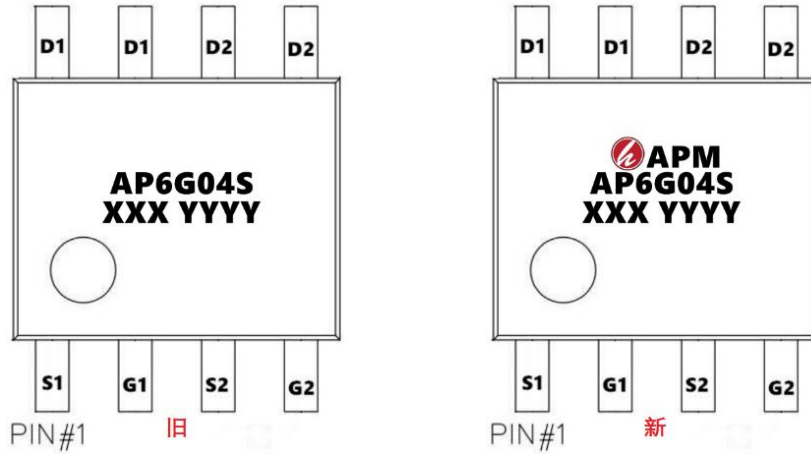
Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
V _{DS}	Drain-Source Voltage	40	-40	V
V _{GS}	Gate-Source Voltage	±20	±20	V
I _D T _c =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	6.3	-6.1	A
I _D T _c =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	4.9	-4.8	A
I _{sw}	Pulsed Drain Current ²	23	-22	A
E _{AS}	Single Pulse Avalanche Energy ³	16.2	39	mJ
I _{AS}	Avalanche Current	6.8	-6.8	A
P _D T _c =25°C	Total Power Dissipation ⁴	1.67	1.67	W
T _{stg}	Storage Temperature Range	-55 to 150	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	-55 to 150	°C
R _{thJC}	Thermal Resistance Junction-Ambient ¹	7.5		°C/W
R _{thJC}	Thermal Resistance Junction-Case ¹	30		°C/W

AP6G04S RVE1.0 永源微电子科技有限公司

Product Change Notice(PNC)

为了更好地提升品牌形象和对终端客户使用负责。从 2022 年 9 月 18 号起，针对所有 SOP 系列，PDFN 系列，TO 系列新增 APMlogo，和 APM 标识。示意图如下



届时会存在不带 logo 和带 logo 两种丝印并存，但是两种产品均为原装正品。

同时永源微电子 将于 2022 年 12 月后将启用永源微电子新的包装设计。如有给各位带来困扰还请所有客户见谅。

